



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

0755-83047638

ysbdt@szyoushang.cn

www.szyoushang.cn



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Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of automotive applications.

Feature

- $BV_{CEO} > 60V$
- $I_C = 1A$ Continuous Collector Current
- $I_{CM} = 2A$ Peak Pulse Current
- $R_{CE(SAT)} = 195m\Omega$ for a Low Equivalent On-Resistance
- 500mW Power Dissipation
- h_{FE} Characterized up to 2A for High Current Gain Hold Up
- Complementary PNP Type: NK-FMMT591Q

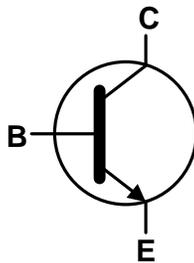
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 
- Weight 0.008 grams (Approximate)

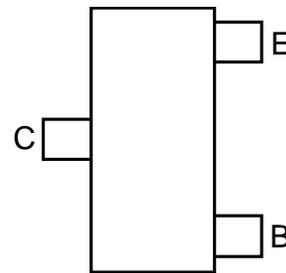
SOT23 (Type DN)



Top View



Device Symbol



Top View
Pin-Out

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	80	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	I _C	1	A
Peak Pulse Current	I _{CM}	2	A
Base Current	I _B	200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

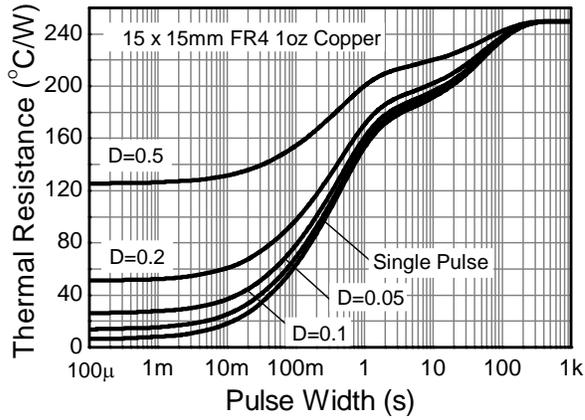
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P _D	500	mW
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	250	°C/W
Thermal Resistance, Junction to Lead (Note 7)	R _{θJL}	197	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 8)

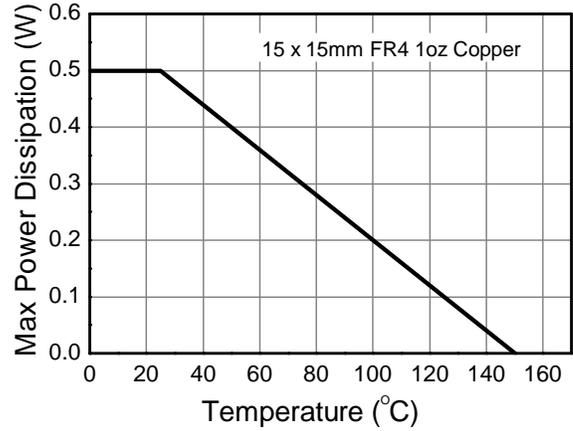
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	C

- Notes:
6. For a device mounted with the collector lead on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 7. Thermal resistance from junction to solder-point (at the end of the collector lead).
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

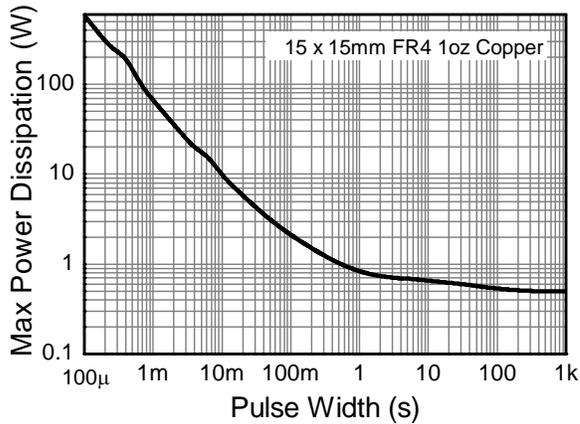
Thermal Characteristics and Derating Information



Transient Thermal Impedance



Derating Curve



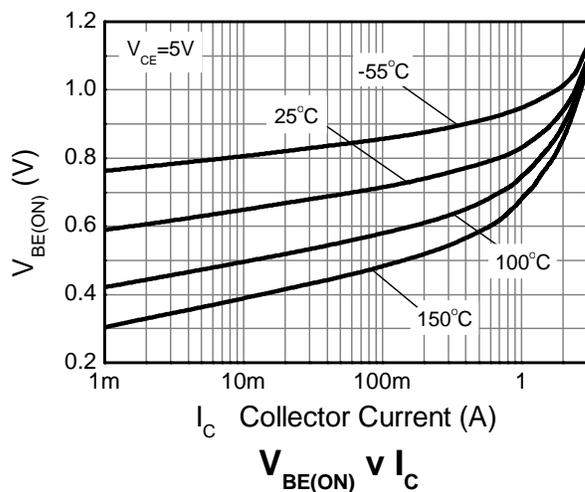
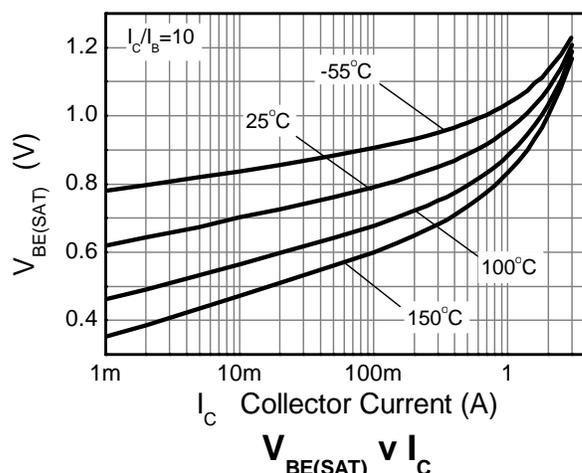
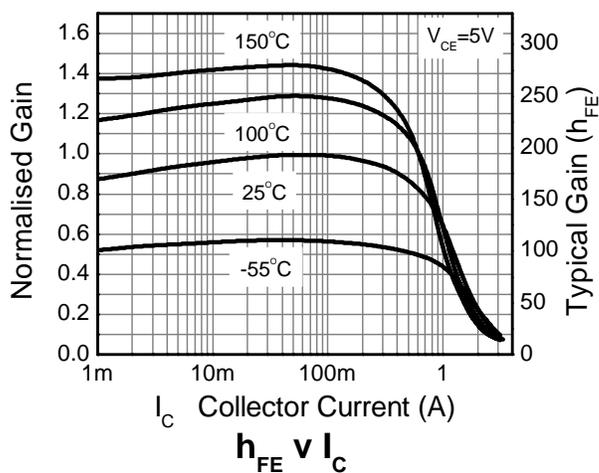
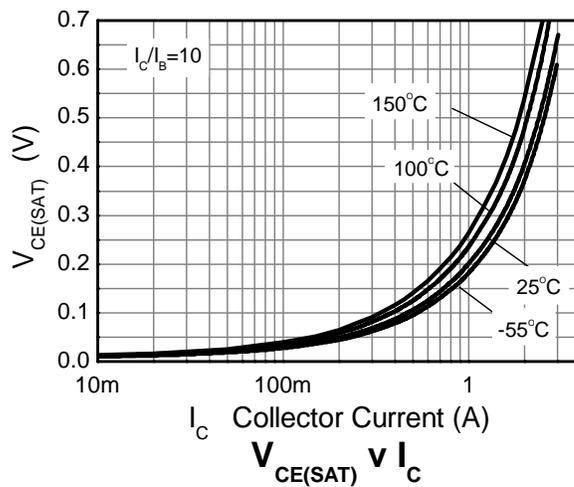
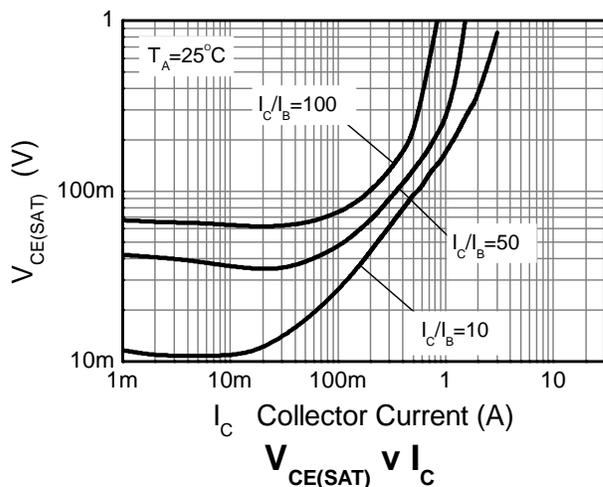
Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	80	—	—	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	60	—	—	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.1	—	V	I _E = 100μA
Collector Cutoff Current	I _{CBO}	—	<1	100	nA	V _{CB} = 60V
Emitter Cutoff Current	I _{EBO}	—	<1	100	nA	V _{EB} = 5.6V
Collector Emitter Cutoff Current	I _{CES}	—	<1	100	nA	V _{CE} = 60V, V _{CES} = 60V
Static Forward Current Transfer Ratio (Note 9)	h _{FE}	100	140	—	—	I _C = 1mA, V _{CE} = 5V
		100	150	300		I _C = 500mA, V _{CE} = 5V
		80	120	—		I _C = 1A, V _{CE} = 5V
		30	40	—		I _C = 2A, V _{CE} = 5V
Collector-Emitter Saturation Voltage (Note 9)	V _{CE(SAT)}	—	100	150	mV	I _C = 500mA, I _B = 50mA
		—	160	250		I _C = 1A, I _B = 100mA
Base-Emitter Turn-On Voltage (Note 9)	V _{BE(ON)}	—	830	1,000	mV	I _C = 1A, V _{CE} = 5V
Base-Emitter Saturation Voltage (Note 9)	V _{BE(SAT)}	—	965	1,100	mV	I _C = 1A, I _B = 100mA
Output Capacitance	C _{OBO}	—	—	10	pF	V _{CB} = 10V, f = 1MHz
Transition Frequency	f _T	150	—	—	MHz	V _{CE} = 10V, I _C = 50mA, f = 100MHz

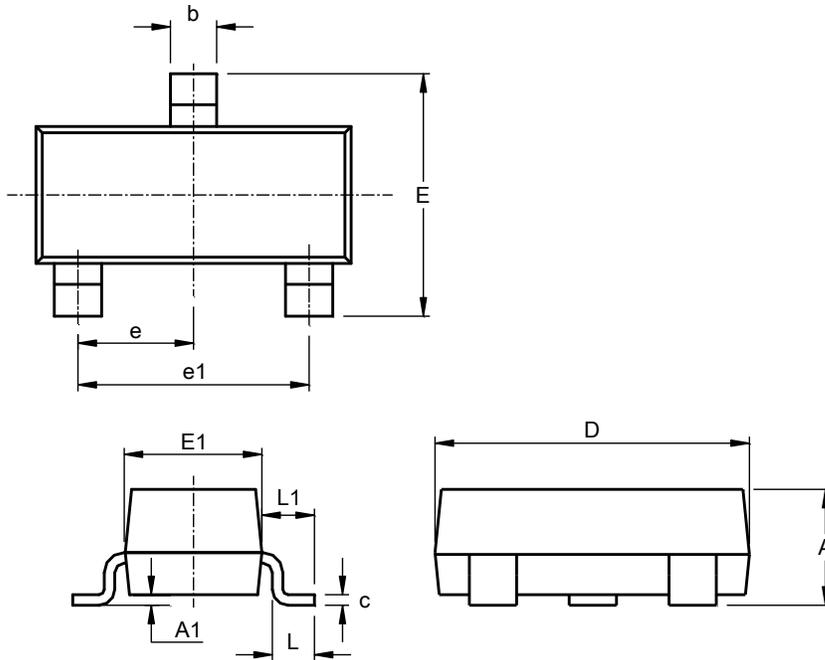
Note: 9. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



Package Outline Dimensions

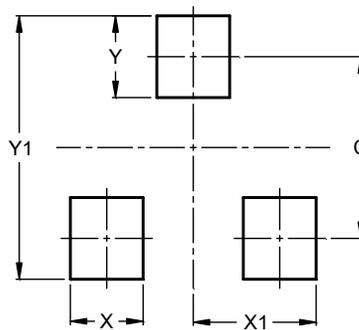
SOT23 (Type DN)



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Dim	Min	Max	Typ
A	0.89	1.12	1.00
A1	0.01	0.10	0.05
b	0.30	0.51	0.45
c	0.08	0.20	0.10
D	2.80	3.04	3.00
E	2.10	2.64	2.42
E1	1.20	1.40	1.37
e	0.95 REF		
e1	1.90 REF		
L	0.25	0.60	0.30
L1	0.45	0.62	0.54
All Dimensions in mm			

Suggested Pad Layout

SOT23 (Type DN)



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9